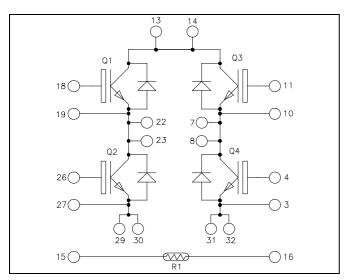
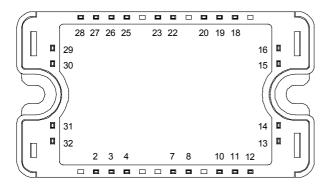


Full - Bridge Trench + Field Stop IGBT3 Power Module





All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

$V_{CES} = 600V$ $I_C = 75A$ @ $T_C = 80^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
ī	Continuous Collector Current	$T_C = 25^{\circ}C$	100	
I_{C}	Continuous Conector Current	$T_C = 80$ °C	75	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	250	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	150A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www microsemi.com

1 - 6



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	W
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C = 75A$	$T_j = 150$ °C		1.7		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C =$	600μΑ	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	= 0V			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$			4620		_
C_{oes}	Output Capacitance	$V_{CE} = 25V$			300		pF
C_{res}	Reverse Transfer Capacitance	f=1MHz			140		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ing (25°C)		110		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 75A$			200		
T_{f}	Fall Time	$R_G = 4.7\Omega$			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$			120		ns
T_{r}	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75A$			250		
$T_{\rm f}$	Fall Time	$R_G = 4.7\Omega$			60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25$ °C		0.35		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 300V$	$T_{j} = 150^{\circ}C$		0.6		1113
E_{off}	Turn-off Switching Energy	$I_C = 75A$	$T_j = 25^{\circ}C$		2.2		mJ
Lott	Turn-on Switching Energy	$R_G = 4.7\Omega$	$T_{j} = 150^{\circ}C$		2.6		1113

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25$ °C			250	μΑ
1KM	Waximum Reverse Leakage Current	V _R GOOV	$T_j = 150$ °C			500	μπ
I_{F}	DC Forward current		$Tc = 80^{\circ}C$		75		A
V_{F}	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_i = 25$ °C		1.6	2	
V F	Blode I of ward Voluge	$V_{GE} = 0V$	$T_i = 150$ °C		1.5		V
t _{rr}	Reverse Recovery Time	Proof of the second se	$T_j = 25$ °C		100		ns
۲r	Reverse Recovery Time			150		115	
Q_{rr}	Reverse Recovery Charge	$V_R = 300V$	$T_j = 25$ °C		3.6		μС
Qrr			$T_{j} = 150^{\circ}C$		7.6		μС
E_{r}	Reverse Recovery Energy		$T_i = 25^{\circ}C$		0.85		mJ
\mathbf{L}_{f}	Reverse Recovery Ellergy		$T_{j} = 150^{\circ}C$		1.8		1113



 $Temperature\ sensor\ NTC\ (\text{see application note APT0406 on www.microsemi.com for more information}).$

Symbol	Characteristic	Min	Тур	Max	Unit	
R ₂₅	Resistance @ 25°C		50		kΩ	
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K	

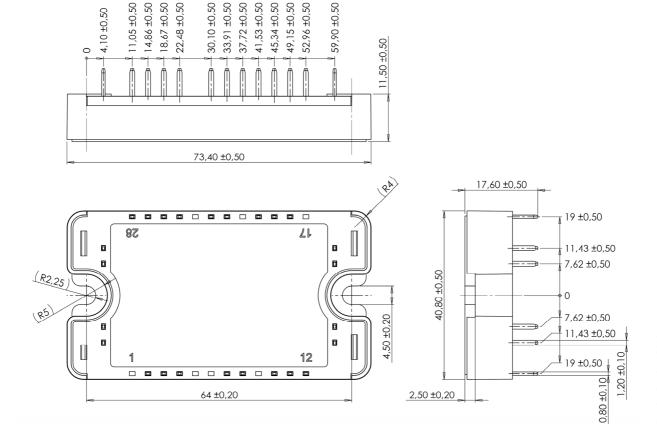
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Mın	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	IG	IGBT			0.60	°C/W
TthJC	Junction to Case Thermal Resistance	Diode				0.98	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T_{J}	Operating junction temperature range		-40		175		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

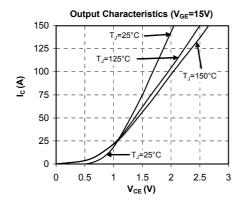
SP3 Package outline (dimensions in mm)

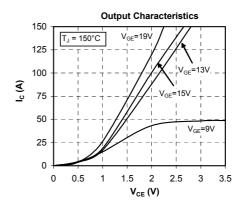


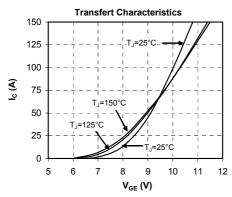
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

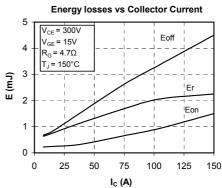


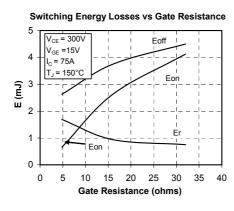
Typical Performance Curve

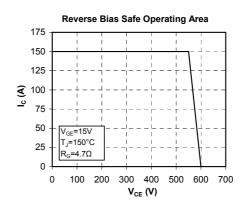


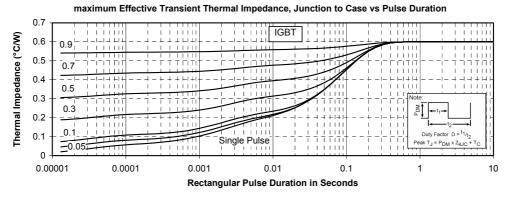




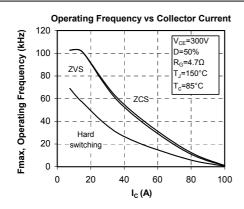


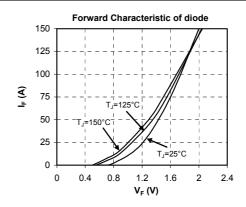


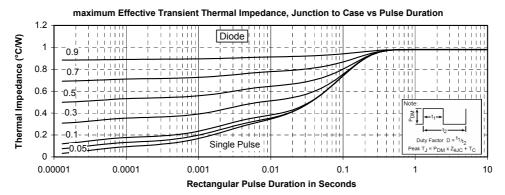












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